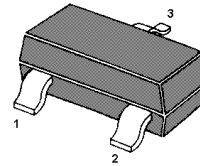


MMBTSA1015

PNP Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into three groups O, Y and G, according to its DC current gain. As complementary type the NPN transistor MMBTSC1815 is recommended.



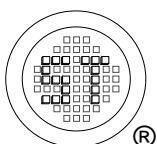
1.BASE 2.EMITTER 3.COLLECTOR
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	50	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	150	mA
Base Current	$-I_B$	50	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 65 to +150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit	
DC Current Gain at $-V_{CE} = 6\text{ V}$, $-I_C = 2\text{ mA}$ at $-V_{CE} = 6\text{ V}$, $-I_C = 150\text{ mA}$	Current Gain Group O	h_{FE}	70	140	-
	Y	h_{FE}	120	240	-
	G	h_{FE}	200	400	-
		h_{FE}	25	-	-
Collector Base Cutoff Current at $-V_{CB} = 50\text{ V}$	$-I_{CBO}$	-	0.1	μA	
Emitter Base Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	0.1	μA	
Collector Base Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	50	-	V	
Collector Emitter Breakdown Voltage at $-I_C = 10\text{ mA}$	$-V_{(BR)CEO}$	50	-	V	
Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-	V	
Collector Emitter Saturation Voltage at $-I_C = 100\text{ mA}$, $-I_B = 10\text{ mA}$	$-V_{CE(sat)}$	-	0.3	V	
Base Emitter Saturation Voltage at $-I_C = 100\text{ mA}$, $-I_B = 10\text{ mA}$	$-V_{BE(sat)}$	-	1.1	V	
Gain Bandwidth Product at $-V_{CE} = 10\text{ V}$, $-I_C = 1\text{ mA}$	f_T	80	-	MHz	
Output Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{OB}	-	7	pF	



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ISO/TS 18949 : 2008
Certificate No. 16073000



ISO14001 : 2004
Certificate No. 7116



ISO 9001 : 2008
Certificate No. 50719410



BS-OHSAS 18001 : 2007
Certificate No. 7116



IECQ QC 080000
Certificate No. PRC-HSPM-1485-1

MMBTSA1015

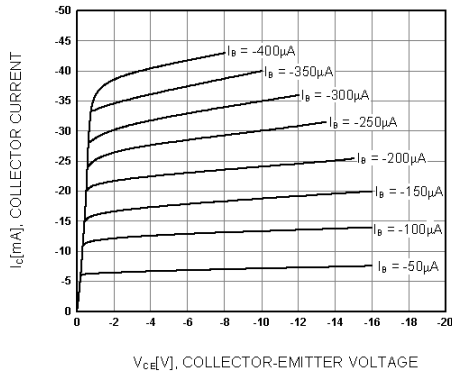


Figure 1. Static Characteristic

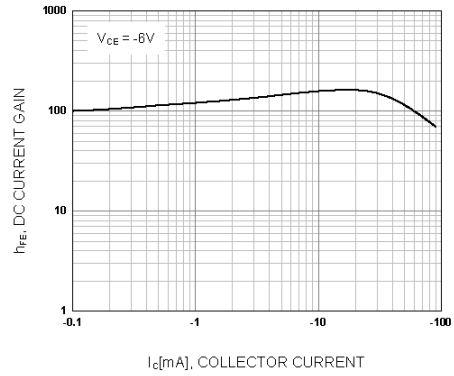


Figure 2. DC current Gain

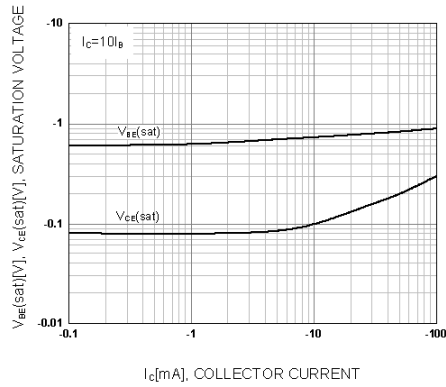


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

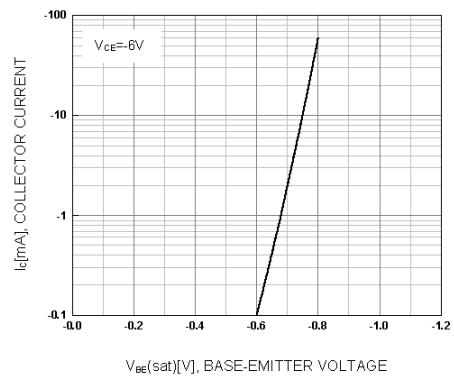


Figure 4. Base-Emitter On Voltage

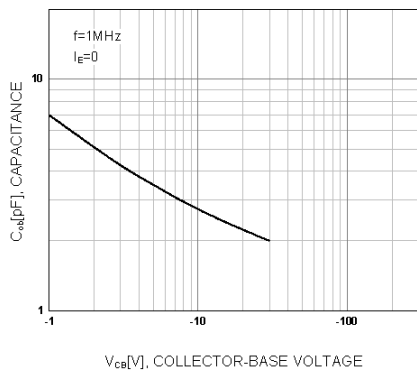


Figure 5. Collector Output Capacitance

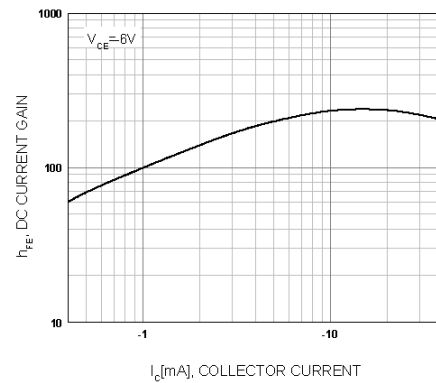
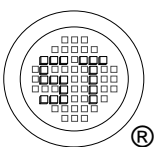


Figure 6. Current Gain Bandwidth Product



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